



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



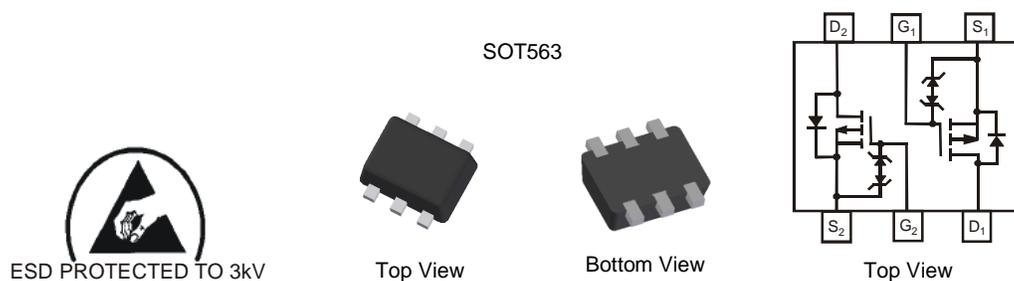
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Features

- Dual P-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package

Mechanical Data

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish - Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)



Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	± 6	V
Continuous Drain Current (Note 4) $V_{GS} = -4.5\text{V}$	Steady State	$T_A = 25^\circ\text{C}$	I_D	-1.03	A
		$T_A = 85^\circ\text{C}$		-0.68	
Pulsed Drain Current (Note 5)			I_{DM}	-3	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P_D	530	mW
Thermal Resistance, Junction to Ambient @ $T_A = 25^\circ\text{C}$ (Note 4)	$R_{\theta JA}$	235	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV_{DSS}	-20	-	-	V	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$	
Zero Gate Voltage Drain Current $T_J = 25^\circ\text{C}$	I_{DSS}	-	-	-100	nA	$V_{DS} = -20\text{V}, V_{GS} = 0\text{V}$	
Gate-Source Leakage	I_{GSS}	-	-	± 2.0	μA	$V_{GS} = \pm 4.5\text{V}, V_{DS} = 0\text{V}$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	$V_{GS(th)}$	-0.5	-	-1.0	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	
Static Drain-Source On-Resistance	$R_{DS(on)}$	-	0.5	0.75	Ω	$V_{GS} = -4.5\text{V}, I_D = -430\text{mA}$	
			0.7	1.05			$V_{GS} = -2.5\text{V}, I_D = -300\text{mA}$
			1.0	1.5			$V_{GS} = -1.8\text{V}, I_D = -150\text{mA}$
			-	20			$V_{GS} = -1.7\text{V}, I_D = -100\text{mA}$
			-	25			$V_{GS} = -1.5\text{V}, I_D = -100\text{mA}$
Forward Transfer Admittance	$ Y_{fs} $	-	0.9	-	S	$V_{DS} = -10\text{V}, I_D = -250\text{mA}$	
Diode Forward Voltage	V_{SD}	-	-0.8	-1.2	V	$V_{GS} = 0\text{V}, I_S = -150\text{mA}$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C_{iss}	-	59.76	-	pF	$V_{DS} = -16\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$	
Output Capacitance	C_{oss}	-	12.07	-	pF		
Reverse Transfer Capacitance	C_{rss}	-	6.36	-	pF		
Total Gate Charge	Q_g	-	622.4	-	pC	$V_{GS} = -4.5\text{V}, V_{DS} = -10\text{V}, I_D = -250\text{mA}$	
Gate-Source Charge	Q_{gs}	-	100.3	-	pC		
Gate-Drain Charge	Q_{gd}	-	132.2	-	pC		
Turn-On Delay Time	$t_{D(on)}$	-	5.1	-	ns	$V_{DD} = -10\text{V}, V_{GS} = -4.5\text{V}, R_L = 47\Omega, R_G = 10\Omega, I_D = -200\text{mA}$	
Turn-On Rise Time	t_r	-	8.1	-	ns		
Turn-Off Delay Time	$t_{D(off)}$	-	28.4	-	ns		
Turn-Off Fall Time	t_f	-	20.7	-	ns		

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 - Repetitive rating, pulse width limited by junction temperature.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

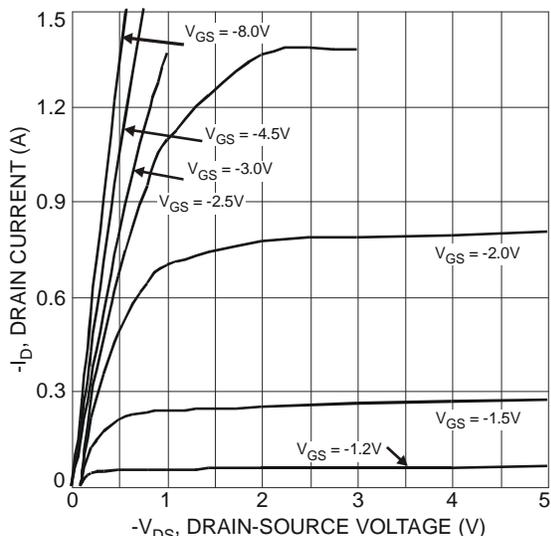


Fig. 1 Typical Output Characteristic

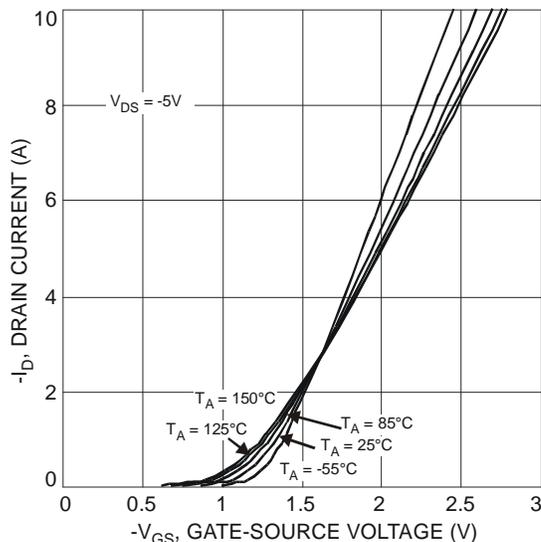


Fig. 2 Typical Transfer Characteristic

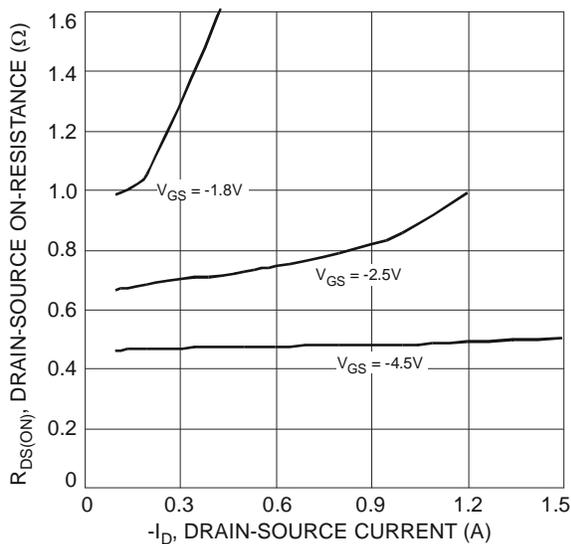


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

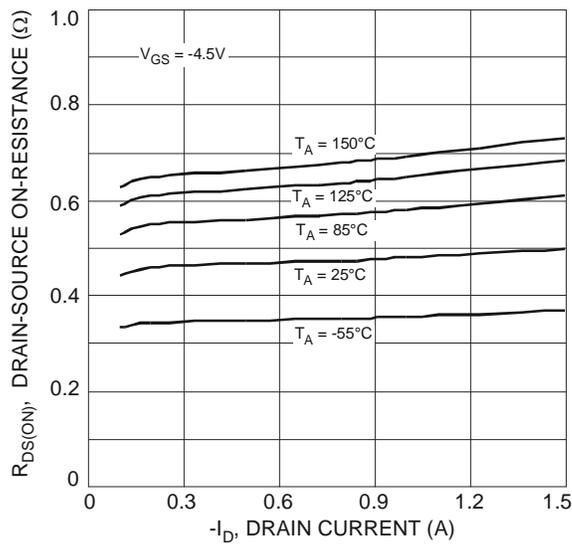


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

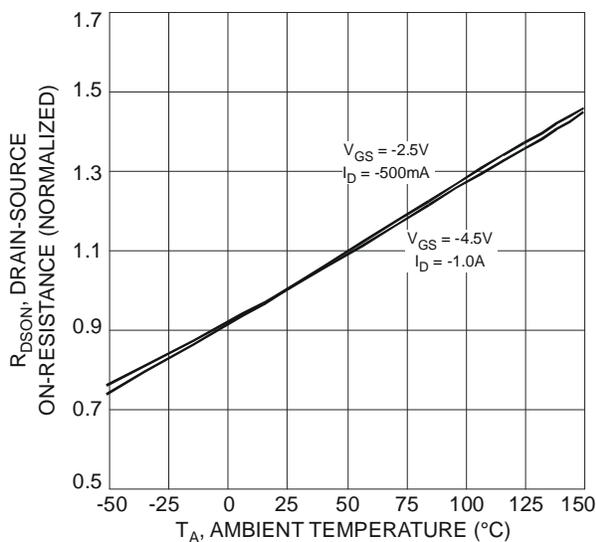


Fig. 5 On-Resistance Variation with Temperature

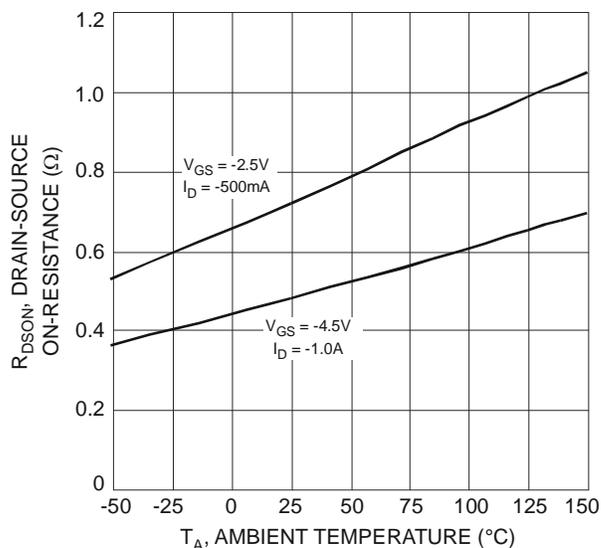


Fig. 6 On-Resistance Variation with Temperature

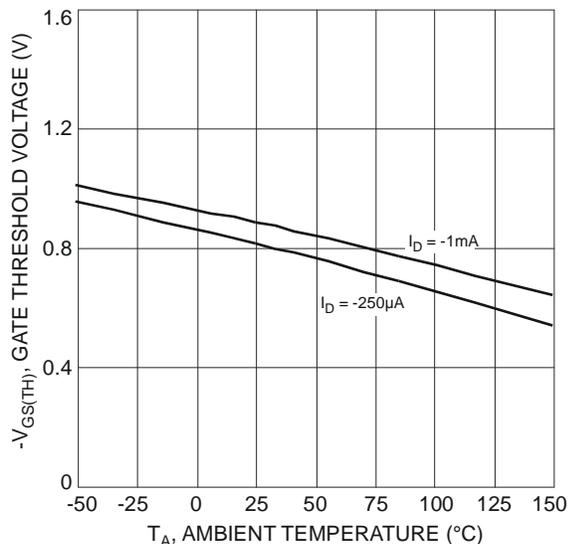


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

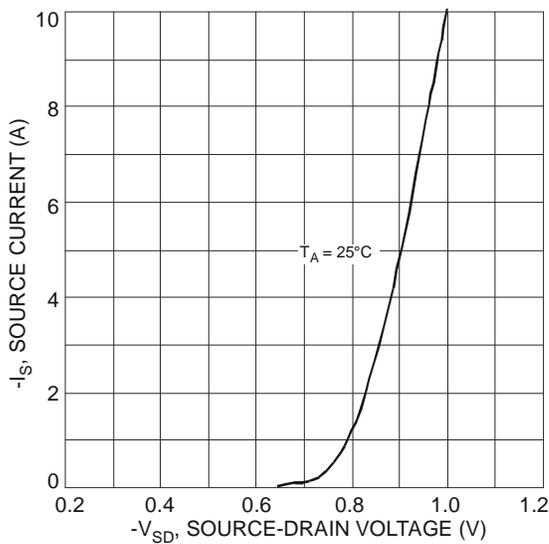


Fig. 8 Diode Forward Voltage vs. Current

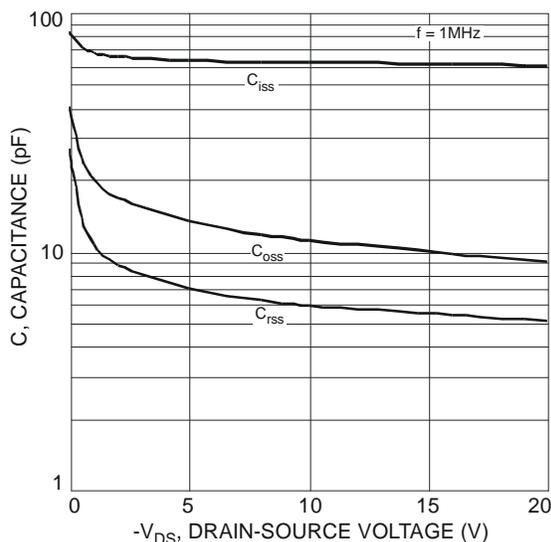


Fig. 9 Typical Total Capacitance

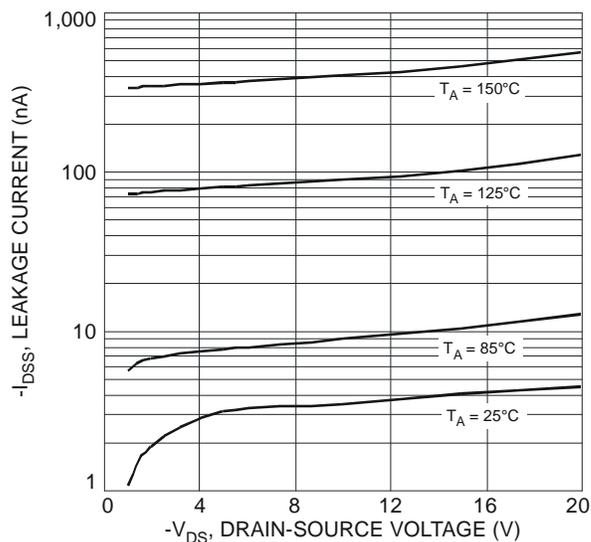


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

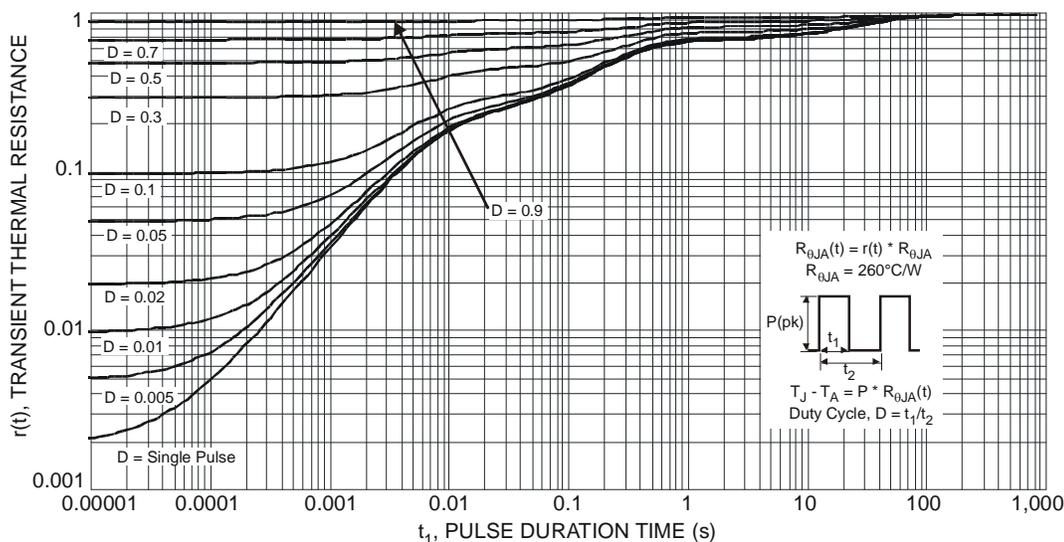
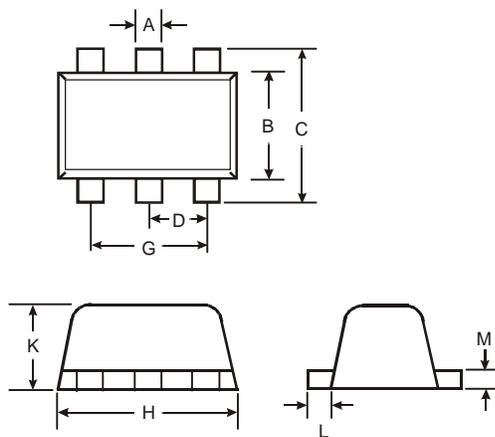


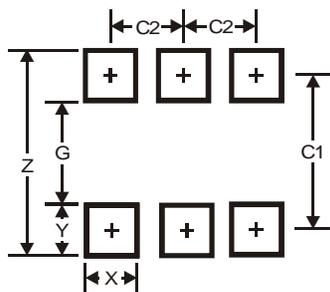
Fig. 11 Transient Thermal Response

Package Outline Dimensions



SOT563			
Dim	Min	Max	Typ
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	-	-	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5